

## 2N5400



### PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring high voltages. Sourced from Process 74. See 2N5401 for characteristics.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V
V <sub>CBO</sub>	Collector-Base Voltage	130	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5400	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier

(continued)

2N5400

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
--------	-----------	-----------------	-----	-----	-------

### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	120		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	130		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 100 \text{ V}, I_E = 0$ $V_{CB} = 100 \text{ V}, I_E = 0, T_A = 100 \text{ }^\circ\text{C}$		100	nA $\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		50	nA

### ON CHARACTERISTICS\*

$h_{FE}$	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 50 \text{ mA}$	30 40 40	180	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.2 0.5	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		1.0 1.0	V V

### SMALL SIGNAL CHARACTERISTICS

$C_{ob}$	Output Capacitance	$V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz}$		6.0	pF
$f_T$	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	100	400	
$h_{fe}$	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	30	200	
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 250 \mu\text{A},$ $R_S = 1.0 \text{ k}\Omega,$ $f = 10 \text{ Hz to } 15.7 \text{ kHz}$		8.0	V

\*Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$